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Abstract of the Disclosure

A method of forming a MOS or CMOS device on a silicon substrate, includes preparing a substrate to contain conductive regions having device active areas therein; forming a gate electrode on the active areas; depositing and forming a gate electrode sidewall insulator layer on 5 each gate electrode; implanting ions of a first type to form a source region and a drain region in one active area and implanting ions of a second type to form a source region and a drain region in the other active area.

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